

### Silicon Epitaxial Planar Schottky Barrier Diode

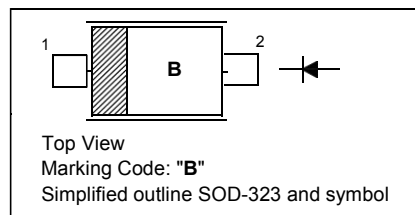
for low current rectification and high speed switching applications

#### Features

- Extremely small surface mounting type
- High reliability

#### PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



#### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Reverse Voltage	$V_R$	30	V
Mean Rectifying Current	$I_{F(AV)}$	200	mA
Peak Forward Surge Current (60 Hz for 1 Cyc.)	$I_{FSM}$	1	A
Junction Temperature	$T_j$	125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 40 to + 125	$^\circ\text{C}$

#### Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 200\text{ mA}$	$V_F$	0.6	V
Reverse Current at $V_R = 10\text{ V}$	$I_R$	1	$\mu\text{A}$

Note: ESD sensitive product handling required.

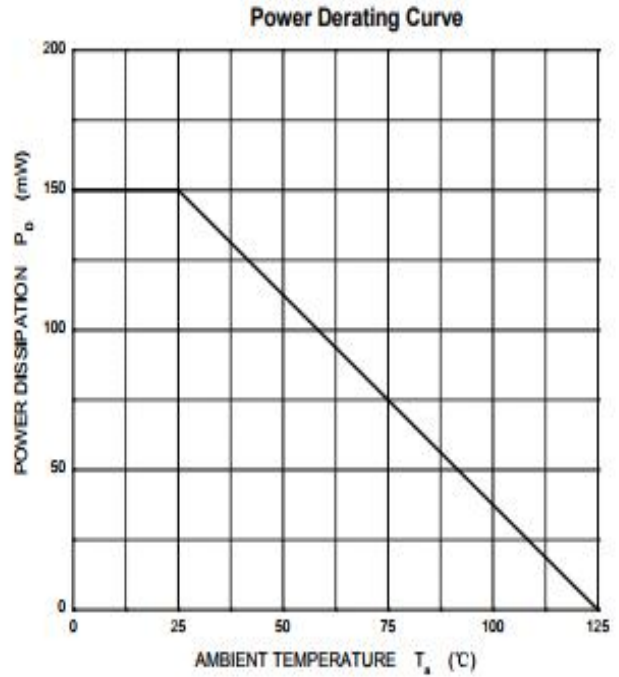
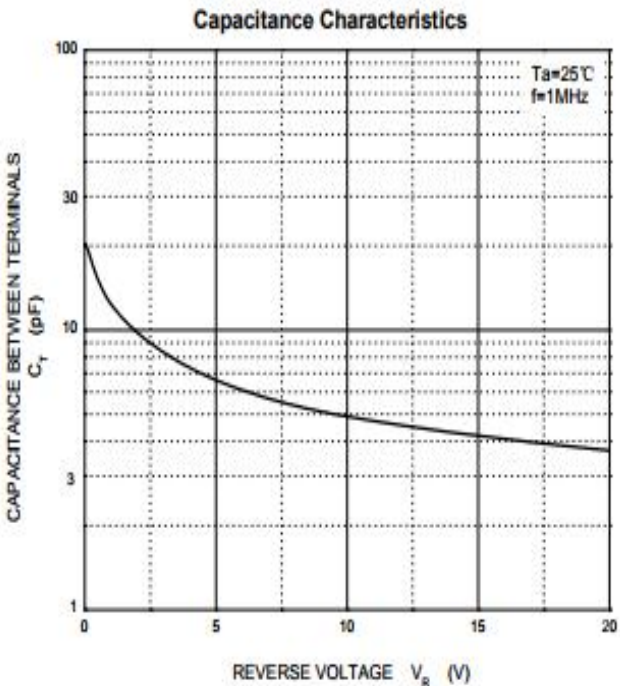
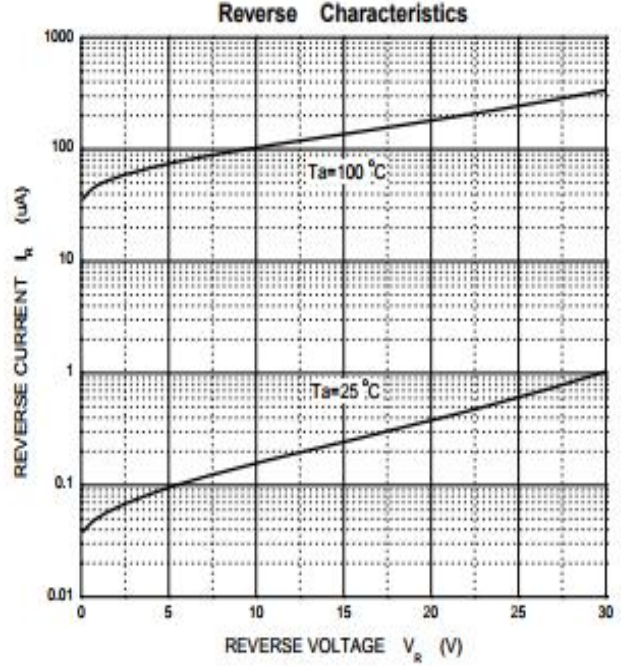
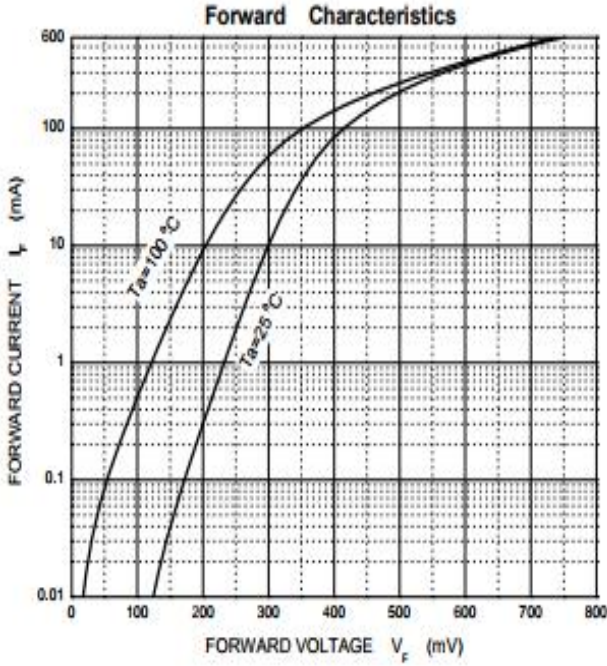


CHINA BASE  
INTERNATIONAL

# SOD-323 RB520SW-30



www.china-base.com.hk

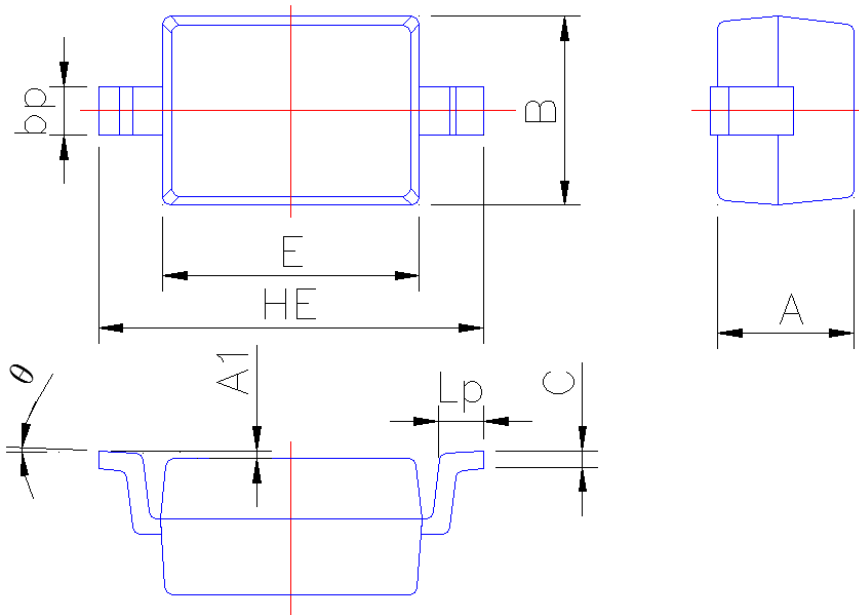




## PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323



Symbol	Dimension in Millimeters	
	Min	Max
A	0.95	1.15
A1	0.010	0.100
B	1.20	1.40
bp	0.25	0.40
C	0.09	0.150
E	1.60	1.80
HE	2.30	2.70
Lp	0.20	0.40
$\theta$	0°	5°